# MICROWAVE POWER GAN HEMT

#### **FEATURES**

•BROAD BAND INTERNALLY MATCHED HEMT •HIGH POWER Pout= 51.0dBm at Pin= 44.0dBm (Pulse: PW=100µs, Duty=10%)

Pout= 48.5dBm at Pin= 42.0dBm (CW)

#### ·HIGH GAIN

GL= 11.0dB at Pin= 20.0dBm (Pulse: PW=100µs, Duty=10%)

•LOW INTERMODULATION DISTORTION WITH WIDE SPACING TONE IM3(Min.)= -25dBc at Pout= 43.0dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE

MICROWAVE SEMICONDUCTOR TECHNICAL DATA



## RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Peak Output Power	Pout	VDS= 40V IDSset= 0.8A f = 13.75 to 14.5GHz @Pin= 44dBm PW=100μs, Duty=10%	dBm	50.0	51.0	_
Peak Drain Current	IDS1		А	_	7.5	9.5
Peak Power Added Efficiency	ηadd1		%		33	
Linear Gain	GL	@Pin= 20dBm PW=100μs, Duty=10%	dB	10.0	11.0	_
Gain flatness	ΔG		dB			±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test @Po=43.0dBm (Single Carrier Level) ∆f= 5MHz(IM3) ∆f= 150MHz, f=14.1GHz (IM3-2)	dBc	-25		
	IM3-2		dBc	-25		
Drain Current	IDS2		А	_	4.0	5.0
Power Gain	Gp2		dB	_	7.5	_
Power Added Efficiency	ηadd2		%	_	20	
Channel Temperature Rise *1	∆Tch		°C		120	160

\*1: Channel Temperature Rise( $\Delta$ Tch) : (VDS×IDS2+Pin(two tone)-Po(two tone))×Rth(c-c) Recommended Gate Resistance (Rg): 10  $\Omega$ 

## ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 30mA	V	-2.0	-3.0	-5.0
Gate-Source Breakdown Voltage	VGSO	IGS= -25mA	V	-10		_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		0.9	1.1

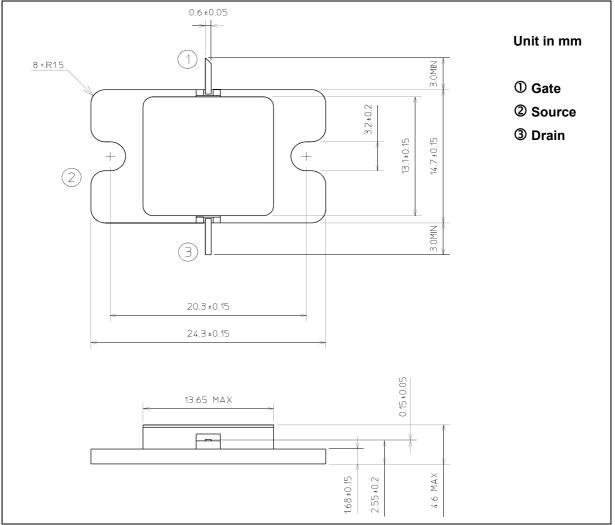
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# MICROWAVE SEMICONDUCTOR TECHNICAL DATA

## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	12.0
Total Power Dissipation (Tc= 25°C)	PT	W	182
Channel Temperature	Tch	°C	225
Storage Temperature	Tstg	°C	-65 to +175

# PACKAGE OUTLINE (7-AA13A)



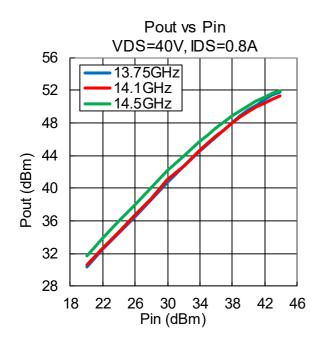
## HANDLING PRECAUTIONS FOR PACKAGE MODEL

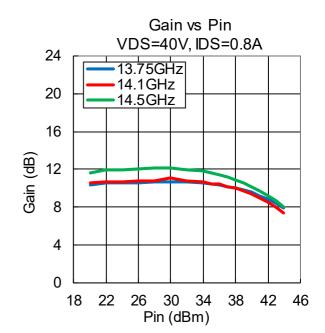
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

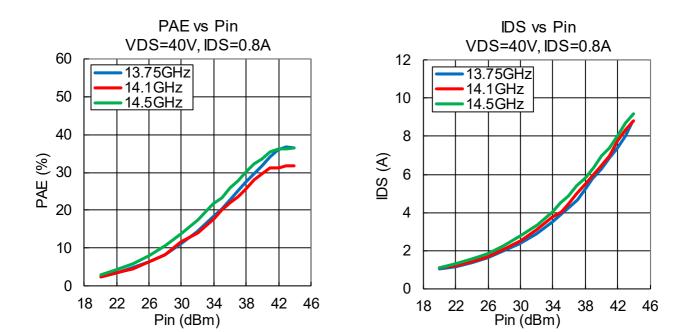
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

### ·Pout , Gain , PAE , IDS vs. Pin (Pulse: PW=100us, Duty=10%)

VDS= 40 V, IDSset= 0.8 A, f= 13.75, 14.1, 14.5 GHz, Ta= +25 °C





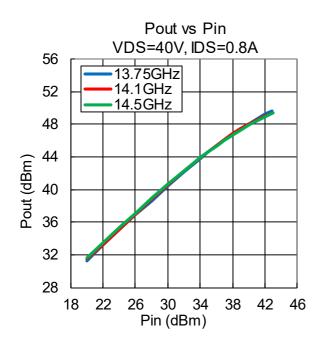


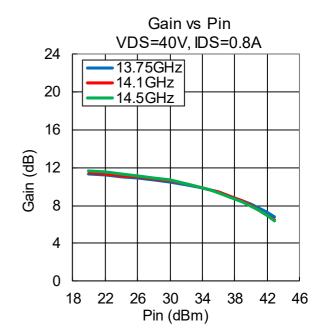
MICROWAVE POWER GaN HEMT TGI1314-100LPHA

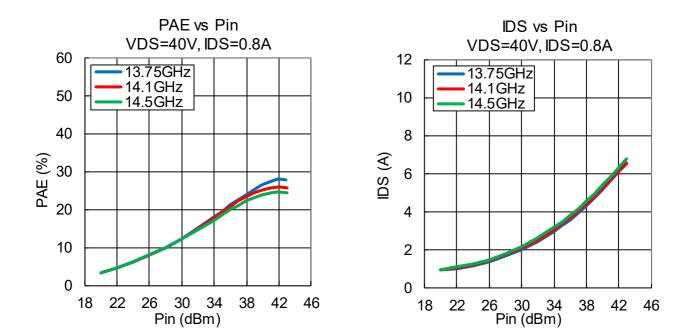
# MICROWAVE SEMICONDUCTOR TECHNICAL DATA

Pout , Gain , PAE , IDS vs. Pin (CW)

VDS= 40 V, IDSset= 0.8 A, f= 13.75, 14.1, 14.5 GHz, Ta= +25 °C





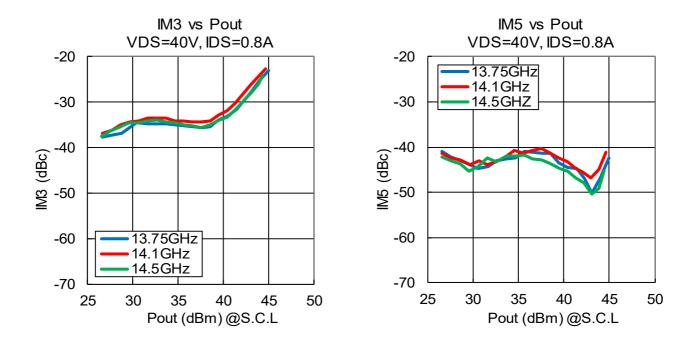


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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

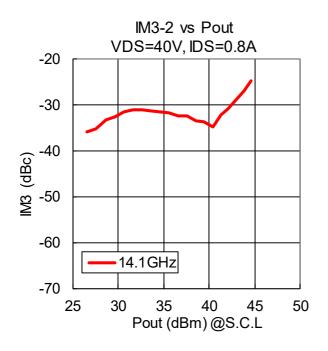
#### ·IM3, IM5 vs. Pout

VDS= 40 V, IDSset= 0.8 A, f= 13.75, 14.1, 14.5 GHz,  $\Delta$ f= 5 MHz , Ta= +25  $^\circ$ C



·IM3-2 vs. Pout

VDS= 40 V, IDSset= 0.8 A, f= 14.1 GHz,  $\Delta$ f= 150 MHz , Ta= +25  $^\circ$ C

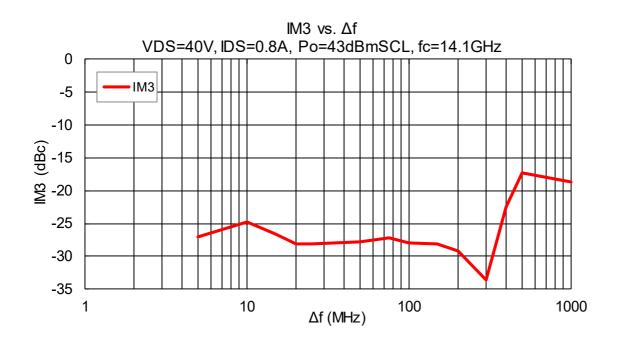




## MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### IM3 vs. ∆f (Two tone spacing)

VDS= 40V, IDSset= 0.8A, f= 14.1GHz, Po= 43dBmSCL, Ta= +25°C

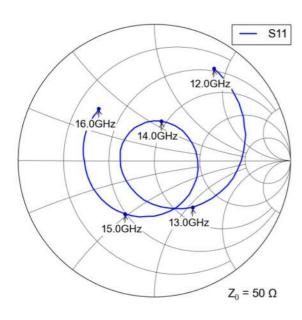


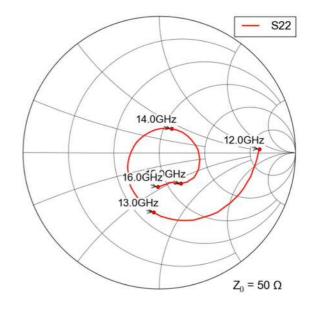
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

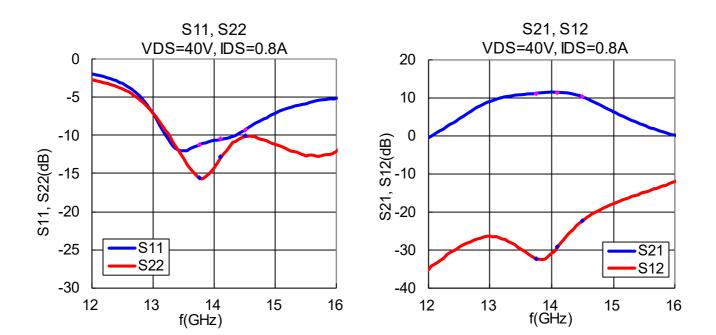
## MICROWAVE POWER GaN HEMT TGI1314-100LPHA

#### ·S-Parameters

VDS= 40 V, IDSset= 0.8 A, f= 12.0 to 16.0 GHz, Ta= +25  $\,^\circ \! \mathbb{C}$ 







MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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